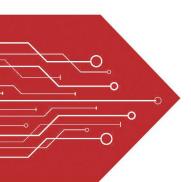
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

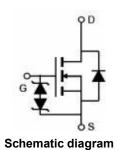
Broduct data sheet













SOT-23

General Features

• $V_{DS} = 20V, I_D = 6.5A$

 $R_{DS(ON)}$ <40m Ω @ V_{GS} =1.8V

 $R_{DS(ON)}$ <33m Ω @ V_{GS} =2.5V

 $R_{DS(ON)}$ <27m Ω @ V_{GS} =4.5V

ESD Rating: 2000V HBM

- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM application
- Load switch

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

| • (• • | , | | |
|--|------------------|------------|------------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | V _G s | ±8 | V |
| Drain Current-Continuous | I _D | 6.5 | Α |
| Drain Current-Pulsed (Note 1) | I _{DM} | 30 | Α |
| Maximum Power Dissipation | P _D | 1.4 | W |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 150 | $^{\circ}$ |

Thermal Characteristic

| Thermal Resistance, Junction-to-Ambient (Note 2) | Reja | 89 | °C/W |
|--|------|----|------|
|--|------|----|------|

Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|--------------------------------|-------------------|--|-----|-----|-----|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250 μA | 20 | | - | V |





Semiconductor

| _ | | | | | | |
|----|---|---|-----|---|---|--|
| റപ | m | n | ıaı | n | ഫ | |

| Zero Gate Voltage Drain Current | IDSS | V _{DS} =20V,V _{GS} =0V | _ | - | 1 | PΑ |
|------------------------------------|---------------------|---|------|-----|-----|----|
| Gate-Body Leakage Current | Igss | V _{GS} =±10V,V _{DS} =0V | _ | _ | ±10 | μA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =250μA | 0.45 | 0.7 | 1.0 | V |
| | | V _{GS} =4.5V, I _D =6.5A | - | 17 | 27 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =2.5V, I _D =5.5A | - | 21 | 33 | mΩ |
| | | V _{GS} =1.8V, I _D =5A | - | 28 | 40 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V,I _D =6.5A | 8 | - | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | Clss | | - | 660 | - | PF |
| Output Capacitance | Coss | V _{DS} =10V,V _{GS} =0V, | - | 160 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | | 87 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 0.5 | | nS |
| Turn-on Rise Time | t _r | V _{DD} =10V,R _L =1. 5Ω | _ | 1 | | nS |
| Turn-Off Delay Time | t _{d(off)} | • | | 12 | | nS |
| Turn-Off Fall Time | t _f | | _ | 4 | | nS |
| Total Gate Charge | Qg | | _ | 8 | | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =10V,I _D =6.5A, | | 2.5 | - | nC |
| Gate-Drain Charge | Qgd | V _{GS} =4.5V | - | 3 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V,I _S =6.5A | _ | - | 1.2 | V |
| Diode Forward Current (Note 2) | ls | | _ | _ | 6.5 | Α |

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

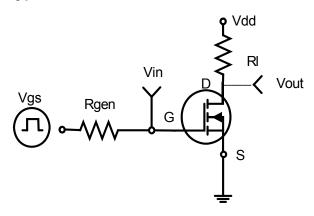


Figure 1:Switching Test Circuit

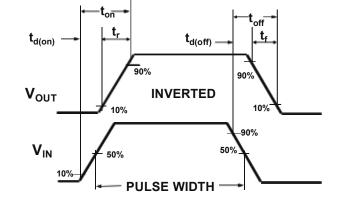
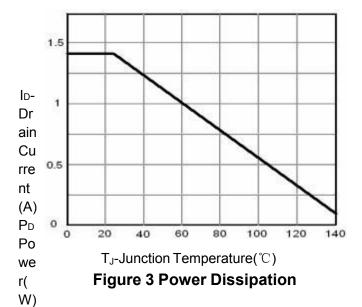


Figure 2:Switching Waveforms



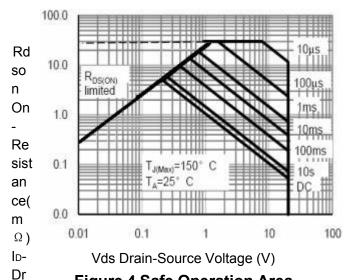


Figure 4 Safe Operation Area

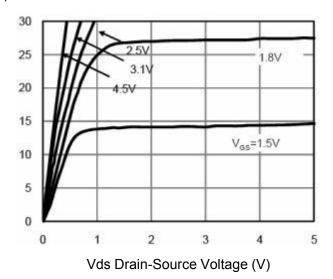


Figure 5 Output Characteristics

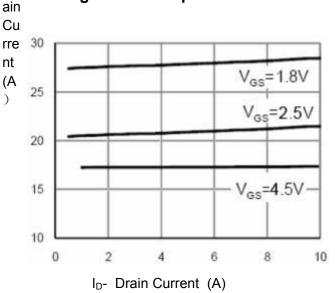


Figure 6 Drain-Source On-Resistance

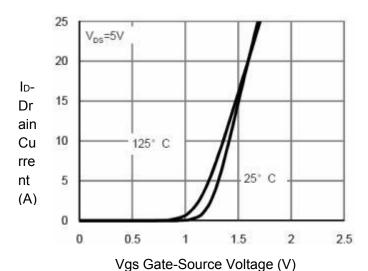
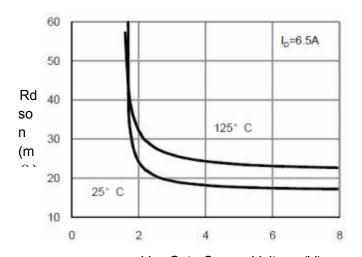


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

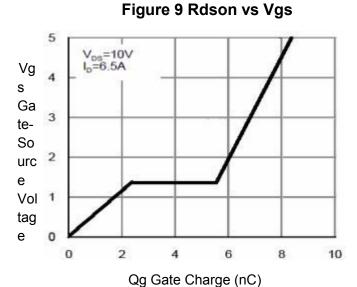


Figure 11 Gate Charge

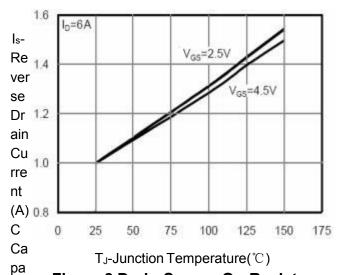


Figure 8 Drain-Source On-Resistance

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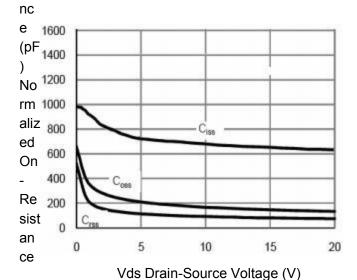


Figure 10 Capacitance vs Vds

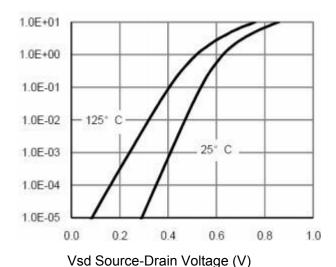


Figure 12 Source- Drain Diode Forward



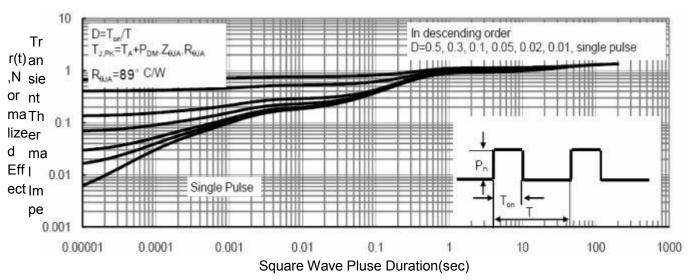
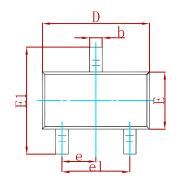
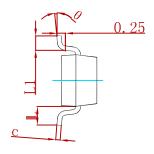


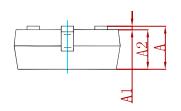
Figure 13 Normalized Maximum Transient Thermal Impedance



PACKAGE MECHANICAL DATA

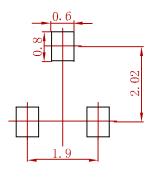






| Symbol | Dimensions | In Millimeters | Dimension | ns In Inches | |
|--------|------------|----------------|-----------|--------------|--|
| Symbol | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| E | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| е | 0.95 | 0.950TYP | | 7TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550REF | | 0.02 | 2REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- General tolerance:±0.05mm.
 The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|--------|--------|------|
| MS3416 | SOT-23 | 3000 |



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DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1_T0_00201 PJMF380N65E1_T0_00201
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